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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

TISP4xxxJ3BJ Overvoltage Protector Series

Ion-Implanted Breakdown Region
-Precise and Stable Voltage
-Low Voltage Overshoot Under Surge

**Designed for Transformer Center Tap (Ground Return)
Overvoltage Protection**
-Enables GR-1089-CORE Compliance
-High Holding Current Allows Protection of Data Lines
 with d.c. Power Feed

**Can be Used to Protect Rugged Modems Designed for Exposed
Applications Exceeding TIA-968-A**

Device Name	V_{DRM} V	$V_{(BO)}$ V
TISP4070J3BJ	58	70
TISP4080J3BJ	65	80
TISP4095J3BJ	75	95
TISP4115J3BJ	90	115
TISP4125J3BJ	100	125
TISP4145J3BJ	120	145
TISP4165J3BJ	135	165
TISP4180J3BJ	145	180
TISP4200J3BJ	155	200
TISP4219J3BJ	180	219
TISP4250J3BJ	190	250
TISP4290J3BJ	220	290
TISP4350J3BJ	275	350
TISP4395J3BJ	320	395

⟳ ....UL Recognized Component

SMB Package (Top View)

MD-SMB-004-a

Device Symbol

SD-TISP4xxx-001-a
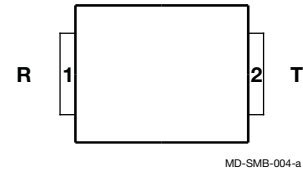
Rated for International Surge Wave Shapes

Wave Shape	Standard	I_{PPSM} A
2/10	GR-1089-CORE	1000
8/20	IEC 61000-4-5	800
10/160	TIA-968-A	400
10/700	ITU-T K.20/21/45	350
10/560	TIA-968-A	250
10/1000	GR-1089-CORE	200

Description

The range of TISP4xxxJ3BJ devices are designed to limit overvoltages on telecom lines. The TISP4xxxJ3BJ is primarily designed to address GR-1089-CORE compliance on data transmission lines with d.c. power feeding. When overvoltage protection is applied to transformer coupled lines from the transformer center tap to ground, the total ground return current can be 200 A, 10/1000 and 1000 A, 2/10. The high 150 mA holding current is set above common d.c. feed system levels to allow the TISP4xxxJ3BJ to reset following a disturbance.

These devices allow signal voltages, without clipping, up to the maximum off-state voltage value, V_{DRM}, see Figure 1. Voltages above V_{DRM} are limited and will not exceed the breakover voltage, $V_{(BO)}$, level. If sufficient current flows due to the overvoltage, the device switches into a low voltage on-state condition, which diverts the current from the overvoltage through the device. When the diverted current falls below the holding current, I_H, level the devices switches off and restores normal system operation.

How to Order

Device	Package	Carrier	Order As	Marking Code	Std. Qty.
TISP4xxxJ3BJ	SMB (DO-214AA)	Embossed Tape Reeled	TISP4xxxJ3BJR-S	4xxxJ3	3000

 Insert xxx value corresponding to device name.

TISP4xxxJ3BJ Overvoltage Protector Series

BOURNS®

Absolute Maximum Ratings, T_A = 25 °C (Unless Otherwise Noted)

Rating		Symbol	Value	Unit
Repetitive peak off-state voltage	'4070J3BJ	V_{DRM}	±58	V
	'4080J3BJ		±65	
	'4095J3BJ		±75	
	'4115J3BJ		±90	
	'4125J3BJ		±100	
	'4145J3BJ		±120	
	'4165J3BJ		±135	
	'4180J3BJ		±145	
	'4200J3BJ		±155	
	'4219J3BJ		±180	
	'4250J3BJ		±190	
	'4290J3BJ		±220	
	'4350J3BJ		±275	
	'4395J3BJ		±320	
Non-repetitive peak impulse current (see Notes 1 and 2)		I_{PPSM}		A
2/10 µs (GR-1089-CORE, 2/10 µs voltage wave shape)			±1000	
8/20 µs (IEC 61000-4-5, combination wave generator, 1.2/50 µsvoltage wave shape)			±800	
10/160 µs (TIA-968-A, 10/160 µs voltage wave shape)			±400	
4/250 µs (ITU-T K.20/21, 10/700 µs voltage waveshape, simultaneous)			±370	
5/310 µs (ITU-T K.20/21, 10/700 µs voltage wave shape, single)			±350	
5/320 µs (TIA-968-A, 9/720 µs voltage waveshape, single)			±350	
10/560 µs (TIA-968-A, 10/560 µs voltage wave shape)			±250	
10/1000 µs (GR-1089-CORE, 10/1000 µs voltage wave shape)			±200	
Non-repetitive peak on-state current (see Notes 1 and 2)		I_{TSM}	50	A
20 ms, 50 Hz (full sine wave)				
Initial rate of rise of on-state current. Linear current ramp. Maximum ramp value < 50 A		di_T/dt	800	A/µs
Junction temperature		T_J	-40 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C

NOTES: 1. Initially the device must be in thermal equilibrium with T_J = 25 °C.
         2. These non-repetitive rated currents are peak values of either polarity. The surge may be repeated after the device returns to its initial conditions.

Electrical Characteristics, T_A = 25 °C (Unless Otherwise Noted)

Parameter		Test Conditions		Min	Typ	Max	Unit
I_{DRM}	Repetitive peak off-state current	$V_D = V_{DRM}$	T_A = 25 °C			±5	µA
			T_A = 85 °C			±10	
$V_{(BO)}$	AC Breakover voltage	dv/dt = ±250 V/ms, R_{SOURCE} = 300 Ω	'4070J3BJ			±70	V
			'4080J3BJ			±80	
			'4095J3BJ			±95	
			'4115J3BJ			±115	
			'4125J3BJ			±125	
			'4145J3BJ			±145	
			'4165J3BJ			±165	
			'4180J3BJ			±180	
			'4200J3BJ			±200	
			'4219J3BJ			±219	
			'4250J3BJ			±250	
			'4290J3BJ			±290	
			'4350J3BJ			±350	
			'4395J3BJ			±395	

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Electrical Characteristics, T_A = 25 °C (Unless Otherwise Noted)

Parameter		Test Conditions		Min	Typ	Max	Unit
$V_{(BO)}$	Ramp breakover voltage	dv/dt ≤ ±1000 V/µs, Linear voltage ramp, Maximum ramp value = ±500 V di/dt = ±20 A/µs, Linear current ramp, Maximum ramp value = ±10 A	'4070J3BJ			±77	V
			'4080J3BJ			±88	
			'4095J3BJ			±104	
			'4115J3BJ			±125	
			'4125J3BJ			±135	
			'4145J3BJ			±156	
			'4165J3BJ			±177	
			'4180J3BJ			±192	
			'4200J3BJ			±212	
			'4219J3BJ			±231	
			'4250J3BJ			±263	
			'4290J3BJ			±303	
			'4350J3BJ			±364	
			'4395J3BJ			±409	
$I_{(BO)}$	Breakover current	dv/dt = ±250 V/ms, R_{SOURCE} = 300 Ω	'4070J3BJ thru '4115J3BJ			±900	mA
			'4125J3BJ thru '4219J3BJ			±800	
			'4250J3BJ thru '4395J3BJ			±600	
I_H	Holding current	I_T = ±5 A, di/dt = ±30 mA/ms		±150		±600	mA
dv/dt	Critical rate of rise of off-state voltage	Linear voltage ramp Maximum ramp value < 0.85V_{DRM}		±5			kV/µs
I_D	Off-state current	V_D = ±50 V	T_A = 85 °C			±10	µA
C_O	Off-state capacitance	f = 1 MHz, V_d = 1 V rms, V_D = 0	'4070J3BJ thru '4115J3BJ		195	235	pF
			'4125J3BJ thru '4219J3BJ		120	145	
			'4250J3BJ thru '4395J3BJ		105	125	
		f = 1 MHz, V_d = 1 V rms, V_D = -1 V	'4070J3BJ thru '4115J3BJ		180	215	
			'4125J3BJ thru '4219J3BJ		110	132	
			'4250J3BJ thru '4395J3BJ		95	115	
		f = 1 MHz, V_d = 1 V rms, V_D = -2 V	'4070J3BJ thru '4115J3BJ		165	200	
			'4125J3BJ thru '4219J3BJ		100	120	
			'4250J3BJ thru '4395J3BJ		90	105	
		f = 1 MHz, V_d = 1 V rms, V_D = -50 V	'4070J3BJ thru '4115J3BJ		85	100	
			'4125J3BJ thru '4219J3BJ		50	60	
			'4250J3BJ thru '4395J3BJ		42	50	
		f = 1 MHz, V_d = 1 V rms, V_D = -100 V (see Note 3)	'4125J3BJ thru '4219J3BJ		40	50	
			'4250J3BJ thru '4395J3BJ		35	40	

NOTE: 3. To avoid possible clipping, the TISP4125J3BJ is tested with V_D = -98 V.

Thermal Characteristics

Parameter		Test Conditions	Min	Typ	Max	Unit
$R_{\theta JA}$	Junction to ambient thermal resistance	EIA/JESD51-3 PCB, I_T = $I_{TSM(1000)}$ (see Note 4)			90	°C/W

NOTE: 4. EIA/JESD51-2 environment and PCB has standard footprint dimensions connected with 5 A rated printed wiring track widths.
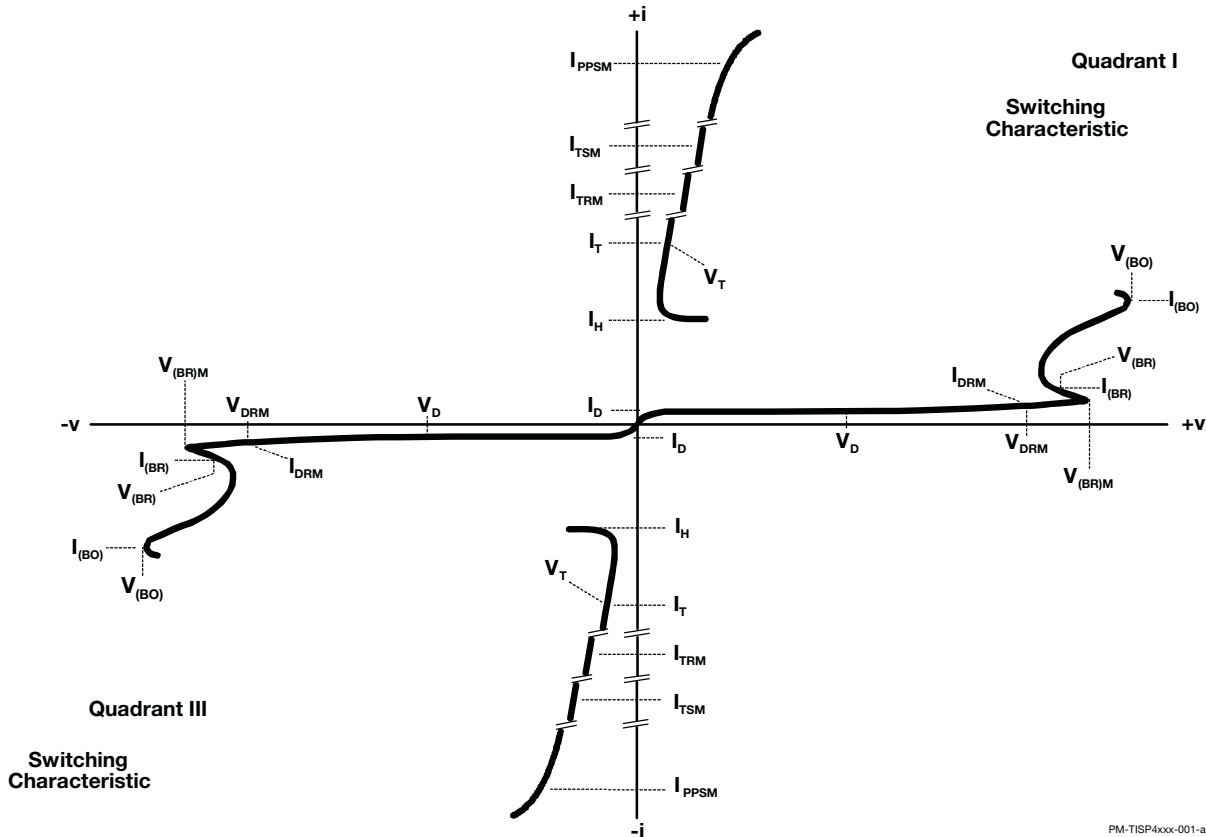
Parameter Measurement Information

PM-TISP4xxx-001-a

Figure 1. Voltage-Current Characteristic for T and R Terminals
All Measurements are Referenced to the R Terminal

Typical Characteristics

OFF-STATE CURRENT
vs
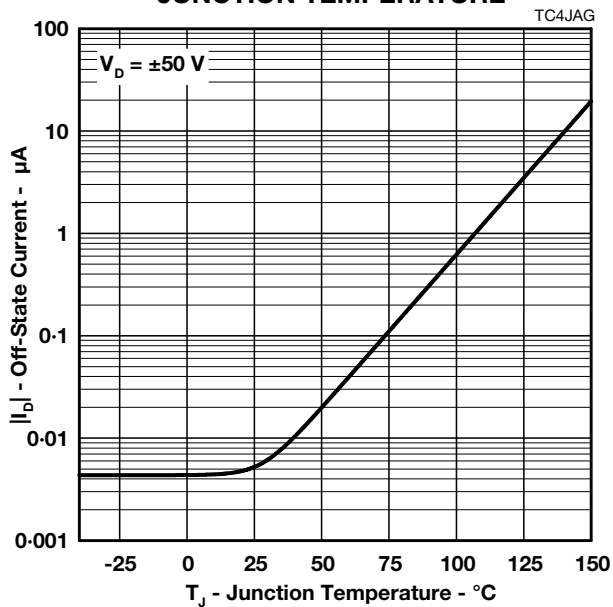### JUNCTION TEMPERATURE

TC4JAG

$V_D = \pm 50\ V$

$|I_D|$ - Off-State Current - μA

T_J - Junction Temperature - °C

Figure 2.

NORMALIZED BREAKOVER VOLTAGE
vs
JUNCTION TEMPERATURE

TC4JAF

Normalized Breakover Voltage

T_J - Junction Temperature - °C
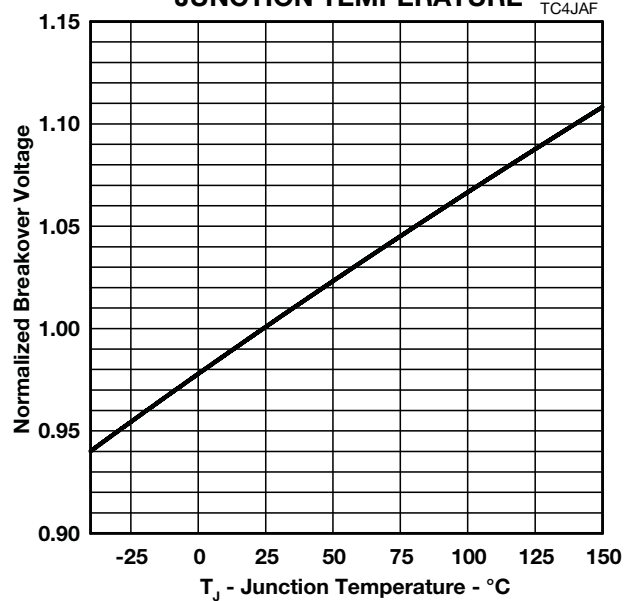
Figure 3.

NORMALIZED HOLDING CURRENT
vs
JUNCTION TEMPERATURE

TC4JAD

Normalized Holding Current

T_J - Junction Temperature - °C
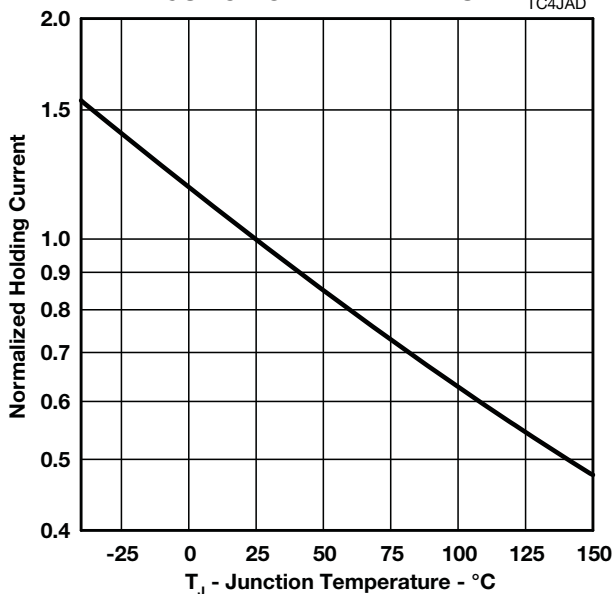
Figure 4.

NORMALIZED CAPACITANCE
vs
OFF-STATE VOLTAGE
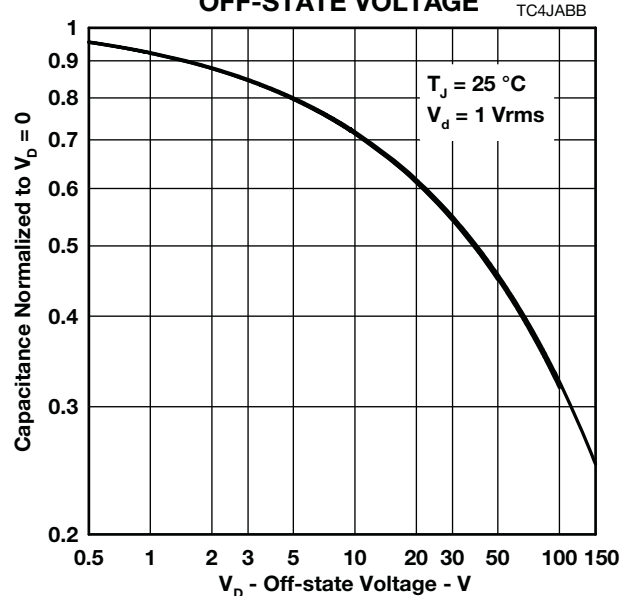
TC4JABB

$T_J = 25\ °C$
$V_d = 1\ Vrms$

Capacitance Normalized to $V_D = 0$

V_D - Off-state Voltage - V

Figure 5.

Rating and Thermal Characteristics

NON-REPETITIVE PEAK ON-STATE CURRENT
vs
CURRENT DURATION

TI4JAA

V_{GEN} = 600 Vrms, 50/60 Hz
R_{GEN} = 1.4*V_{GEN}/$I_{TSM(t)}$
EIA/JESD51-2 ENVIRONMENT
EIA/JESD51-3 PCB
T_A = 25 °C

$I_{TSM(t)}$ - Non-Repetitive Peak On-State Current - A

t - Current Duration - s
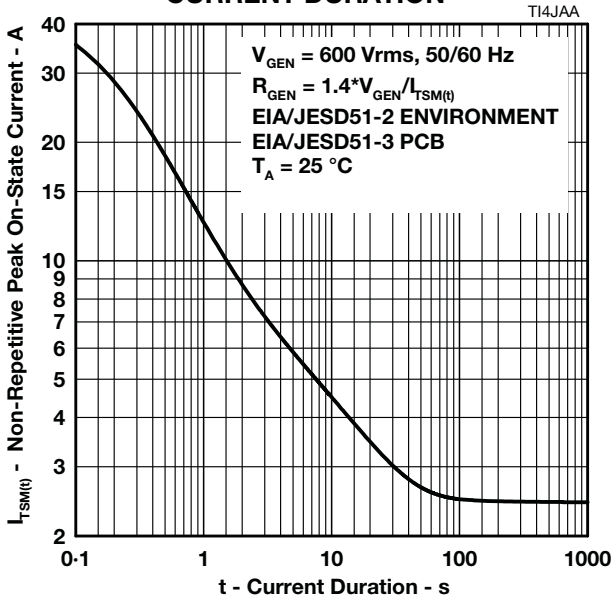
Figure 6.

V_{DRM} DERATING FACTOR
vs
MINIMUM AMBIENT TEMPERATURE

TI4JADCa

Derating Factor

'4070J3BJ thru '4115J3BJ

'4125J3BJ thru '4219J3BJ

'4250J3BJ thru '4395J3BJ

$T_{A(MIN)}$ - Minimum Ambient Temperature - °C
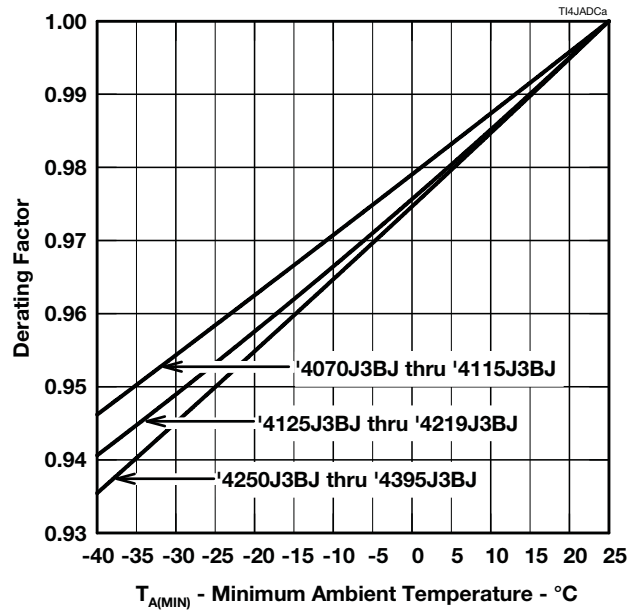
Figure 7.

Applications Information
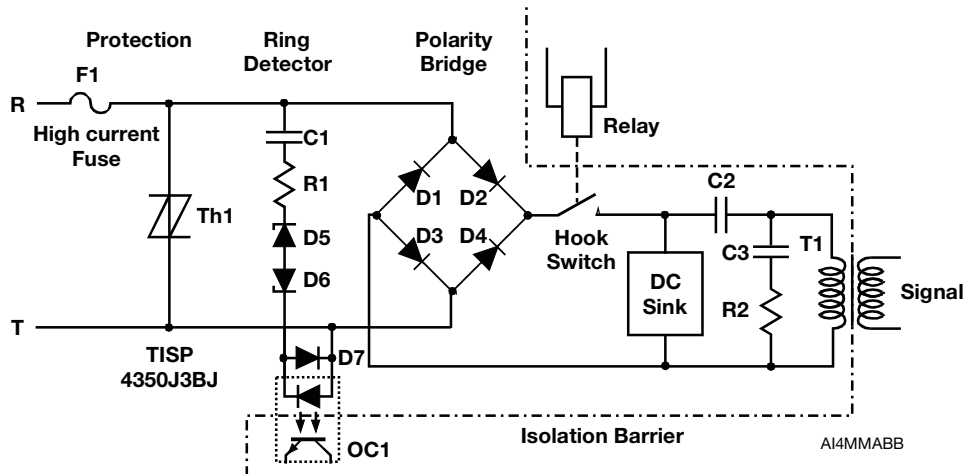
Figure 8. Typical Application Circuit
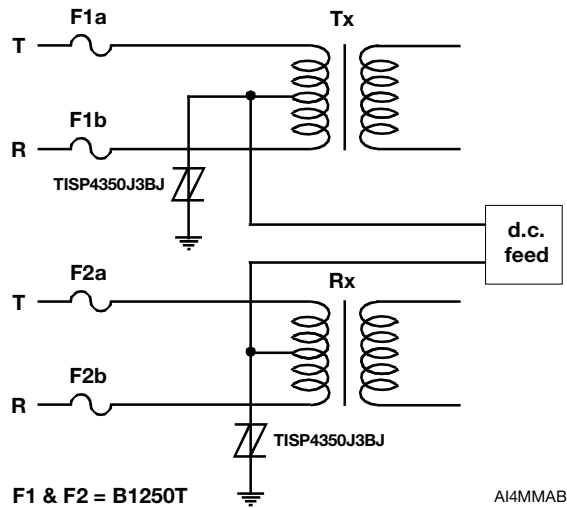
Figure 9. Typical Application Circuit